L Number	Hits	Search Text	DB	Time stamp
-	7998	385/88-94.ccls. 257/80-82,431-433.ccls.	USPAT;	2004/07/09 14:24
	',,,,		US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	3652	(385/88-94.ccls. 257/80-82,431-433.ccls.) and circuit\$5	USPAT;	2004/07/09 12:09
		(US-PGPUB;	
	Ì		EPO; JPO;	
			DERWENT	
-	3258	385/88-94.ccls.	USPAT;	2004/07/09 14:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	2544	385/88-94.ccls. not (((385/88-94.ccls. 257/80-82,431-433.ccls.) and	USPAT;	2004/07/12 10:17
		circuit\$5) and (diodes lasers light adj emitters))	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	1857	385/88-94.ccls. not (((385/88-94.ccls. 257/80-82,431-433.ccls.) and	USPAT;	2004/07/12 10:15
		circuit\$5) and (diodes lasers light adj emitters))	US-PGPUB;	
			EPO; JPO;	
		205/00 04 1	DERWENT	
-	1857	385/88-94.ccls. not (((385/88-94.ccls. 257/80-82,431-433.ccls.) and	USPAT;	2004/07/12 10:17
		circuit\$5) and (diodes lasers light adj emitters))	US-PGPUB;	
			EPO; JPO;	
	2250	205/00 04 1	DERWENT	
-	3258	385/88-94.ccls.	USPAT;	2004/07/12 10:17
			US-PGPUB;	
			EPO; JPO;	
	1201	((205)00 041- 257/00 02 421 4221-) 1 '- '-05' 1 (1'-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-	DERWENT	2004/07/12 10 10
-	1301	((385/88-94.ccls. 257/80-82,431-433.ccls.) and circuit\$5) and (diodes lasers	USPAT;	2004/07/12 10:18
		light adj emitters)	US-PGPUB;	
			EPO; JPO; DERWENT	
 _	2544	385/88-94.ccls. not (((385/88-94.ccls. 257/80-82,431-433.ccls.) and		2004/07/12 10:38
-	2544	circuit\$5) and (diodes lasers light adj emitters))	USPAT; US-PGPUB;	2004/07/12 10.38
		circuits) and (diodes fasers right adj chinters))	EPO; JPO;	
			DERWENT	
-	726	g02b006/43.ipc,epc.	USPAT;	2004/07/12 10:56
	,20	gozooon isiipe,ope.	US-PGPUB;	2004/07/12 10:50
			EPO; JPO;	
			DERWENT	
-	625	g02b006/43.ipc,epc.	EPO; JPO;	2004/07/12 10:48
			DERWENT	
-	239	g02b006/43.ipc,epc.	EPO; JPO	2004/07/12 10:47
-	239	g02b006/43.ipc,epc. (g02b006/43.ipc,epc. not us)	EPO; JPO;	2004/07/12 10:48
	:		DERWENT	
-	239	g02b006/43.ipc,epc.	EPO; JPO	2004/07/12 10:48
-	168	g02b006/43.ipc,epc. not us	EPO; JPO	2004/07/12 10:55
-	386	g02b006/43.ipc,epc.	DERWENT	2004/07/12 10:57
-	67	g02b006/43.ipc,epc. not us	DERWENT	2004/07/12 10:56
-	9368	g02b006/42.ipc,epc.	DERWENT	2004/07/12 11:01
-	5098	g02b006/42.ipc,epc. not us	DERWENT	2004/07/12 10:58
-	9953	g02b006/42.ipc,epc.	EPO; JPO	2004/07/12 11:02
-	15051	g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)	EPO; JPO;	2004/07/12 12:12
		(001 00 (10) (001 00 (10) (001 00 (10) (10	DERWENT	
-	6174	(g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (lead electrode	EPO; JPO;	2004/07/12 11:15
	1000	wiring contact metalliz\$5 conductor\$5 electric\$5)	DERWENT	0004/0=/
-	1836	(g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (lead electrode	EPO; JPO;	2004/07/12 12:13
	Δ .	wiring metalliz\$5 conductor\$5)	DERWENT	2004/05/15 11 11
-	0	mingbou near3 zhou.in.	US-PGPUB	2004/07/12 11:59
-	0	mingbou with zhou.in.	US-PGPUB	2004/07/12 11:59
-	47 2024	ming\$5 with zhou.in.	US-PGPUB	2004/07/12 11:59
-	2024	(g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (lead electrode wiring metalliz\$5 conductor\$5)	EPO; JPO;	2004/07/12 12:20
		wiring metalliz\$5 conductor\$5)	DERWENT	

•	188	((g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (lead electrode	EPO; JPO;	2004/07/12 12:13
		wiring metalliz\$5 conductor\$5)) not ((g02b006/42.ipc,epc.	DERWENT	
		(g02b006/42.ipc,epc. not us)) and (lead electrode wiring metalliz\$5		
		conductor\$5))		
-	6061	(g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (diodes lasers	EPO; JPO;	2004/07/12 12:20
		emitters transducers sources)	DERWENT	
-	5415	((g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (diodes lasers	EPO; JPO;	2004/07/12 12:21
		emitters transducers sources)) not ((g02b006/42.ipc,epc.	DERWENT	
		(g02b006/42.ipc,epc. not us)) and (lead electrode wiring metalliz\$5		
		conductor\$5))		
-	415	(((g02b006/42.ipc,epc. (g02b006/42.ipc,epc. not us)) and (diodes lasers	EPO; JPO;	2004/07/12 12:21
		emitters transducers sources)) not ((g02b006/42.ipc,epc.	DERWENT	
		(g02b006/42.ipc,epc. not us)) and (lead electrode wiring metalliz\$5		
		conductor\$5))) and circuit\$5		
-	330	385/146.ccls.	USPAT;	2004/07/14 09:56
			US-PGPUB	

L Number	Hits	Search Text	DB	Time stamp
•	166	fiber with groov\$5 same reflect\$5 and 385/88-94.ccls.	USPAT;	2004/07/15 15:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	106	fiber with groov\$5 same reflect\$5 and 385/49.ccls.	USPAT;	2004/07/15 15:51
			US-PGPUB;	
			EPO; JPO;	
	410	C1 14 C 40C 1C1 14 0C - 120C/40 00 041-	DERWENT	2004/07/15 16:20
-	419	fiber with reflect\$5 and fiber with groov\$5 and 385/49,88-94.ccls.	USPAT; US-PGPUB;	2004/07/15 16:20
			EPO; JPO;	
			DERWENT	
_	269	(fiber with reflect\$5 and fiber with groov\$5 and 385/49,88-94.ccls.) not	USPAT;	2004/07/15 15:53
		(fiber with groov\$5 same reflect\$5 and 385/88-94.ccls.)	US-PGPUB;	200 110 10 10 10
		(not with give to called the control of the control	EPO; JPO;	
			DERWENT	
-	31	5,163,113	USPAT;	2004/07/15 15:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	0	5515200.PN. adj facet	USPAT;	2004/07/15 15:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	171	"<111>" adj facet	USPAT;	2004/07/15 16:03
			US-PGPUB;	
			EPO; JPO;	
	1	"45" with "<111>" adj facet	DERWENT	2004/07/15 16:04
-	1	45 with <1112 adj facet	USPAT; US-PGPUB;	2004/07/15 16:04
			EPO; JPO;	
ĺ			DERWENT	
_	41	(fiber with reflect\$5 and fiber with groov\$5 and 385/49,88-94.ccls.) and	USPAT;	2004/07/15 16:52
		(grin graded gradient) with fiber	US-PGPUB;	=====================================
		Grand Grand Grand Control of the Con	EPO; JPO;	
			DERWENT	
-	220	splic\$5 with lens with fiber	USPAT;	2004/07/16 14:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	1018	integrat\$5 with circuit with chip with laser	USPAT;	2004/07/16 14:54
			US-PGPUB;	
			EPO; JPO;	
	23	(integrat\$5 with circuit with chip with laser) and 385/88-94,49.ccls.	DERWENT	2004/07/16 14:46
-	23	(integrate) with circuit with chip with laser) and 385/88-94,49.ccis.	USPAT;	2004/07/16 14:46
İ			US-PGPUB; EPO; JPO;	
			DERWENT	
_	429	(integrat\$5 with circuit with chip with laser) and (fiber waveguide)	USPAT;	2004/07/16 14:59
	,,	(The state of the	US-PGPUB;	300 0 // 10 14.07
			EPO; JPO;	
			DERWENT	
	124	integrat\$5 with circuit with chip with laser near3 (array plurality)	USPAT;	2004/07/16 14:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	1189	chip with laser near3 (array plurality)	USPAT;	2004/07/16 16:31
			US-PGPUB;	
			EPO; JPO;	
	C0.77	Cabin midd lane and Command 1 19 No. 1769	DERWENT	2004/07/15 1 - 1 -
-	637	(chip with laser near3 (array plurality)) and (fiber waveguide)	USPAT;	2004/07/16 15:08
			US-PGPUB;	
			EPO; JPO;	
	,	<u> </u>	DERWENT	<u></u>

123					
123 Chip with laser near3 (array plurality) same (circuitS5 amplifS5 driv\$5)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) DERWENT USP-GPUB, EPO, IPO, DE	-	363	chip with laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5)		2004/07/16 16:32
123 Chip with laser near3 (array plurality) ame (circuitS5 amplifS5 drivS5)) not (Chip with laser near3 (array plurality)) and (fiber waveguide)) Chip with laser near3 (array plurality) ame (circuitS5 amplifS5 drivS5) Claser near3 (array plurality) same (circuitS5 amplifS5 drivS5) Claser near3 (array plurality) Clase					
((chip with laser near3 (array plurality)) and (fiber waveguide)					2004/07/16 16 21
Comparison of	-	123			2004/07/16 16:31
DERWENT USPAT; USPA		İ	((chip with laser near3 (array plurality)) and (fiber waveguide))		
0 ((chip with laser near3 (array plurality) same (circuitS5 amplifS5 driv\$5) US-PQ-PUB; PO, JPO, DERWENT USPAT; US-PQ-PUB; PO, JPO, JPO, JPO, JPO, JPO, JPO, JPO,	}				
not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((fiber waveguide)	•		((-1::		2004/07/16 16:21
Cifber waveguide	-	0			2004/07/10 10:31
S638 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) DERWENT USPAT, US-POPUB; POP, IPO, DERWENT USPAT, US-POPUB; POP, IPO, DERWENT USPAT, US-POPUB; POPUB; P				,	
2673 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) and (fiber waveguide) USPAT; USPA			(libel waveguide)	, ,	
- 2673 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5)) and (fiber waveguide) - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 751 substrate) and (fiber waveguide) - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 752 substrate) and (fiber waveguide) - 753 substrate) and (fiber waveguide) - 754 substrate) and (fiber waveguide) - 755 substrate) and (fiber waveguide) - 756 substrate) and (fiber waveguide) - 757 substrate) and (fiber waveguide) - 758 substrate) and (fiber waveguide) - 759 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate - 750 substrate) and (fiber waveguide) - 750 substrate - 750 su	l <u>-</u>	5638	laser near3 (array plurality) same (circuit\$5 amplif\$5 driy\$5)	1	2004/07/16 16:33
- 2673 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5)) and (fiber waveguide) - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate - 751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 752 substrate) and (fiber waveguide) - 753 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 754 substrate) and (fiber waveguide) - 755 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 756 substrate) and (fiber waveguide) - 757 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same - 758 substrate) and (fiber waveguide) - 759 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 751 laser adj diodes with (gaas galium adj arsenide) - 751 laser adj diodes with (gaas galium adj arsenide) - 752 laser adj diodes with (gaas galium adj arsenide) - 753 laser adj diodes with (gaas galium adj arsenide) - 754 laser adj diodes with (gaas galium adj arsenide) - 755 laser adj diodes with (gaas galium adj arsenide) - 755 laser adj diodes with (gaas galium adj arsenide) - 756 laser adj diodes with (gaas galium adj arsenide) - 757 laser adj diodes with (gaas galium adj arsenide) - 757 laser adj diodes with (gaas galium adj arsenide) - 758 laser adj diodes with (gaas galium adj arsenide) - 759 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 751 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser adj diodes with (gaas galium adj arsenide) - 750 laser		3050	land hours (array planality) sainte (encurios ampinos arrivos)	,	200 110 110 10155
DERWENT Waveguide) 1					
2673 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5)) and (fiber waveguide) USPAT; US-PGPUB; EPO, IPO, DERWENT USPAT; US-PGPUB USPAT; galium adj arsenide) with substrate ((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate ((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate with typicals and (3725 ccls. 3857s ccls.) and (vsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate with typicals and (3725 ccls. 3857s ccls.) (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate with typicals and (3725 ccls. 3857s ccls.) (vcsel (vertical adj cavity adj surface adj emitt		}			
waveguide waveguide US-PGPUB, EPO, IPO, DERWENT US-PGPUB, EPO, IPO, DERWENT USPAT, USP	-	2673	(laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5)) and (fiber		2004/07/16 16:36
DERWENT 2004/07/16 16:33 2				-	
- 1751 laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate USPAT; US-PGPUB; EPO, IPO, DERWENT substrate) and (fiber waveguide) - 314 ((laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide) - 314 ((laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) - 1234 laser adj diodes with (gaas galium adj arsenide) - 1234 laser adj diodes with (gaas galium adj arsenide) near2 substrate and 385/88-94.ccls 124 laser adj diodes with (gaas galium adj arsenide) near2 substrate and 385/88-94.ccls 125 laser adj diodes with (gaas galium adj arsenide) and 385/88-94.ccls 126 laser adj diodes with (gaas galium adj arsenide) with substrate - 127 laser adj diodes with (gaas galium adj arsenide) with substrate - 128 laser adj diodes with (gaas galium adj arsenide) with substrate - 129 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate - 129 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate - 120 laser adj diodes with (gaas galium adj arsenide) with substrate with yitopial sufface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with yitopial solution and arsenide) with substrate with yitopial solution and arsenide) with substrate with yitopial solution and arsenide) with substrate with yitopial solution and arsenide) with substrate with yitopial solution and arsenide) with substrate with yitopial solution and	l			EPO; JPO;	
US-PCPUB; EPO; JPO; DERWENT USPAT; US-PCPUB USPAT; US-PCPUB US-PCPUB				DERWENT	
- 472 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide) - 314 ((laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) - 1234 laser adj diodes with (gaas galium adj arsenide) - 0 laser adj diodes with (gaas galium adj arsenide) near2 substrate and 385/88-94.ccls. - 0 laser adj diodes with (gaas galium adj arsenide) near2 substrate and 385/88-94.ccls. - 121 laser adj diodes with (gaas galium adj arsenide) and 385/88-94.ccls. - 21 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes with (gaas galium adj arsenide) with substrate - 460 laser adj diodes	-	751	laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate		2004/07/16 16:33
1234 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide) ((laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with laser near3 (array plurality)) and (fiber waveguide) (chip with (gaas galium adj arsenide) near2 substrate and (chip with laser near3 (array plurality)) and (gaas galium adj arsenide) and 385/88-94.ccls. (chip with (gaas galium adj arsenide) with (gaas galium adj arsenide) with substrate (chip with laser) (chip with laser near3 (array plurality) (chip with laser near3 (arr		1			
- 472 (laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide) - 314 ((laser near3 (array plurality) same (circuit\$5 amplif\$5 driv\$5) same substrate) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) not ((chip with laser near3 (array plurality)) and (fiber waveguide)) - 1234 laser adj diodes with (gaas galium adj arsenide) - 0 laser adj diodes with (gaas galium adj arsenide) near2 substrate and 385/88-94.ccls. - 121 laser adj diodes with (gaas galium adj arsenide) and 385/88-94.ccls. - 21 laser adj diodes with (gaas galium adj arsenide) and 385/88-94.ccls. - 21 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 389 (vesel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate) and (372/5 ccls. 385/5 ccls.) (Vecel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical55 (Vesel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (SPAT; 2004/08/20 13:53 10SPAT; 2004/08/20 14:13 10SPAT; 2004/08/20 14:13 10SPAT; 2004/08/20 14:14 10SPAT; 2004/08/20 14:14 10SPAT; 2004/08/20 14:14					
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- 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 399 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate - 226 ((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate ((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate) and (372/\$.ccls. 385/\$.ccls.) - 16 ((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate adj emitting adj laser)) with (gaas galium adj arsenide) with substrate adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical\$5 - 16 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate vith typical\$5 - 16 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate vcsel adj type adj laser adj diode - 2004/08/20 13:53 2004/08/20 13:53 2004/08/20 14:13 2004/08/20 14:14	-	460	laser adi diodes with (gaas galium adi arsenide) with substrate		2004/08/20 13:48
- 370 laser adj diodes with (gaas galium adj arsenide) with substrate - 399 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate - 226 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate) and (372/\$.ccls. 385/\$.ccls.) - 16 (((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate) and (372/\$.ccls. 385/\$.ccls.) and (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical\$5 - 16 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical\$5 - 16 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate - 0 vcsel adj type adj laser adj diode - 0 vcsel adj type adj laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode - 0 vcsel adj2 type adj2 laser adj diode			J		
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- 16 (((vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate) and (372/\$.ccls. 385/\$.ccls.)) and (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical\$5 - 16 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate - 0 vcsel adj type adj laser adj diode - 3 vcsel adj2 type adj2 laser adj diode USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	-	226			2004/08/20 13:50
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(vertical adj cavity adj surface adj emitting adj laser)) with (gaas galium adj arsenide) with substrate with typical\$5 (vcsel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate o vcsel adj type adj laser adj diode vcsel adj2 type adj2 laser adj diode (vertical adj cavity adj surface adj emitting adj laser)) with diode with USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; 2004/08/20 14:14	-	10		·	2004/08/20 13:53
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- 16 (versel (vertical adj cavity adj surface adj emitting adj laser)) with diode with (gaas galium adj arsenide) with substrate 0 versel adj type adj laser adj diode USPAT; US-PGPUB USPAT					
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- 0 vcsel adj type adj laser adj diode USPAT; US-PGPUB USPAT; US-PGPUB USPAT; 2004/08/20 14:14					_0000/20 17.13
- 3 vcsel adj2 type adj2 laser adj diode US-PGPUB USPAT; 2004/08/20 14:14	-	0			2004/08/20 14:14
- 3 vcsel adj2 type adj2 laser adj diode USPAT; 2004/08/20 14:14					
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-	3	vcsel near2 type near2 laser adj diode	US-PGPUB	2004/00/20 14.14
	70		USPAT:	2004/08/20 14:51
-	79	vcsel with type with laser adj diode	,	2004/00/20 14:31
		WC750COCH	US-PGPUB	2004/09/20 14:51
-	ļ l	"6758606"	USPAT;	2004/08/20 14:51
			US-PGPUB	2004/00/20 15 20
-	8	(vcsel vertical adj cavity adj surface adj emitting adj laser) with (wire wiring)	USPAT;	2004/08/20 15:30
		with (IC integrated adj circuit)	US-PGPUB	
-	282	(laser) with (wire wiring) with (IC integrated adj circuit)	USPAT;	2004/08/20 15:53
			US-PGPUB	
-	441	(laser) with (wire wiring) with (IC integrated adj circuit)	USPAT;	2004/08/20 16:38
			EPO; JPO;	
			DERWENT	
-	249	(laser) with (wire wiring) with (IC integrated adj circuit)	EPO; JPO;	2004/08/20 16:11
			DERWENT	
-	299	yamabayashi.in.	EPO; JPO;	2004/08/20 16:12
			DERWENT	
-	47	yamabayashi.in.	USPAT;	2004/08/20 16:12
	,		US-PGPUB	
_	282	(laser) with (wire wiring) with (IC integrated adj circuit)	USPAT;	2004/08/20 16:39
			US-PGPUB	